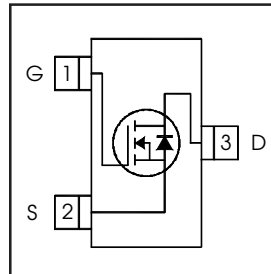


IRLML0100TRPbF

HEXFET® Power MOSFET

| | | |
|--|-------------|-----------|
| V_{DS} | 100 | V |
| V_{GS Max} | ± 16 | V |
| R_{DS(on) max} (@V _{GS} = 10V) | 220 | mΩ |
| R_{DS(on) max} (@V _{GS} = 4.5V) | 235 | mΩ |



Application(s)

- Load/ System Switch

Features and Benefits

Features

| |
|--|
| Industry-standard pinout |
| Compatible with existing Surface Mount Techniques |
| RoHS compliant containing no lead, no bromide and no halogen |
| MSL1 |

results in
 ⇒

Benefits

| |
|----------------------------|
| Multi-vendor compatibility |
| Easier manufacturing |
| Environmentally friendly |
| Increased reliability |

Absolute Maximum Ratings

| Symbol | Parameter | Max. | Units |
|--|---|--------------|-------|
| V _{DS} | Drain-Source Voltage | 100 | V |
| I _D @ T _A = 25°C | Continuous Drain Current, V _{GS} @ 10V | 1.6 | A |
| I _D @ T _A = 70°C | Continuous Drain Current, V _{GS} @ 10V | 1.3 | |
| I _{DM} | Pulsed Drain Current | 7.0 | |
| P _D @ T _A = 25°C | Maximum Power Dissipation | 1.3 | W |
| P _D @ T _A = 70°C | Maximum Power Dissipation | 0.8 | |
| | Linear Derating Factor | 0.01 | |
| V _{GS} | Gate-to-Source Voltage | ± 16 | V |
| T _J , T _{STG} | Junction and Storage Temperature Range | -55 to + 150 | °C |

Thermal Resistance

| Symbol | Parameter | Typ. | Max. | Units |
|------------------|-------------------------------|------|------|-------|
| R _{θJA} | Junction-to-Ambient ③ | — | 100 | °C/W |
| R _{θJA} | Junction-to-Ambient (t<10s) ④ | — | 99 | |

ORDERING INFORMATION:

See detailed ordering and shipping information on the last page of this data sheet.

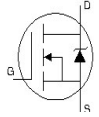
Notes ① through ④ are on page 10

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Electric Characteristics @ T_J = 25°C (unless otherwise specified)

| Symbol | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--|--------------------------------------|------|------|------|-------|--|
| V _{(BR)DSS} | Drain-to-Source Breakdown Voltage | 100 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔV _{(BR)DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | 0.10 | — | V/°C | Reference to 25°C, I _D = 1mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 190 | 235 | mΩ | V _{GS} = 4.5V, I _D = 1.3A ② |
| | | — | 178 | 220 | | V _{GS} = 10V, I _D = 1.6A ② |
| V _{GS(th)} | Gate Threshold Voltage | 1.0 | — | 2.5 | V | V _{DS} = V _{GS} , I _D = 25μA |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 20 | μA | V _{DS} = 100V, V _{GS} = 0V |
| | | — | — | 250 | | V _{DS} = 100V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | V _{GS} = 16V |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | V _{GS} = -16V |
| R _G | Internal Gate Resistance | — | 1.3 | — | Ω | |
| g _{fs} | Forward Transconductance | 5.7 | — | — | S | V _{DS} = 50V, I _D = 1.6A |
| Q _g | Total Gate Charge | — | 2.5 | — | nC | I _D = 1.6A |
| Q _{gs} | Gate-to-Source Charge | — | 0.5 | — | | V _{DS} = 50V |
| Q _{gd} | Gate-to-Drain ("Miller") Charge | — | 1.2 | — | | V _{GS} = 4.5V ② |
| t _{d(on)} | Turn-On Delay Time | — | 2.2 | — | ns | V _{DD} = 50V ② |
| t _r | Rise Time | — | 2.1 | — | | I _D = 1.0A |
| t _{d(off)} | Turn-Off Delay Time | — | 9.0 | — | | R _G = 6.8Ω |
| t _f | Fall Time | — | 3.6 | — | | V _{GS} = 4.5V |
| C _{iss} | Input Capacitance | — | 290 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 27 | — | | V _{DS} = 25V |
| C _{riss} | Reverse Transfer Capacitance | — | 13 | — | | f = 1.0MHz |

Source - Drain Ratings and Characteristics

| Symbol | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|---|------|------|------|-------|--|
| I _S | Continuous Source Current (Body Diode) | — | — | 1.1 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 7.0 | | |
| V _{SD} | Diode Forward Voltage | — | — | 1.3 | V | T _J = 25°C, I _S = 1.1A, V _{GS} = 0V ② |
| t _{rr} | Reverse Recovery Time | — | 20 | 30 | ns | T _J = 25°C, V _R = 50V, I _F = 1.1A |
| Q _{rr} | Reverse Recovery Charge | — | 13 | 20 | nC | di/dt = 100A/μs ② |

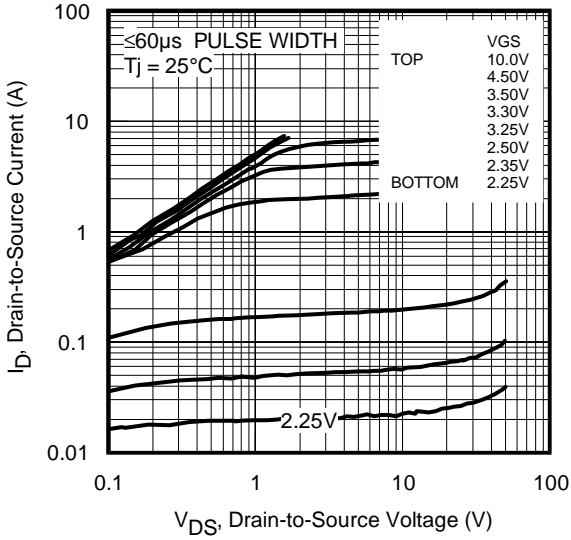


Fig 1. Typical Output Characteristics

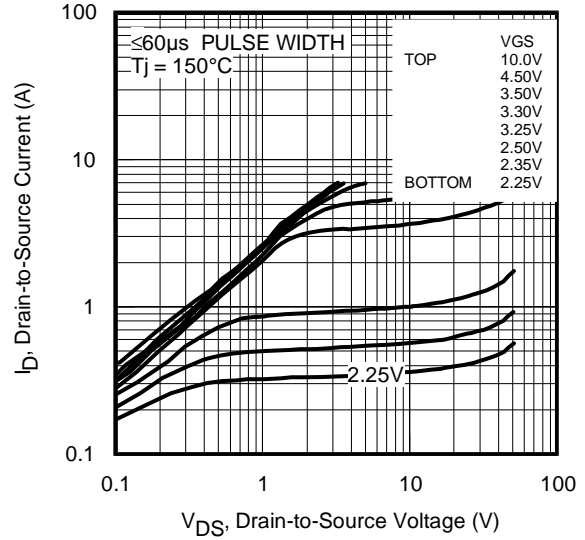


Fig 2. Typical Output Characteristics

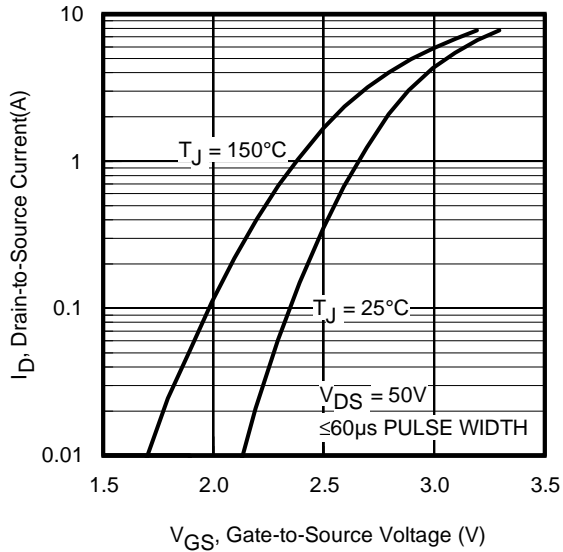


Fig 3. Typical Transfer Characteristics

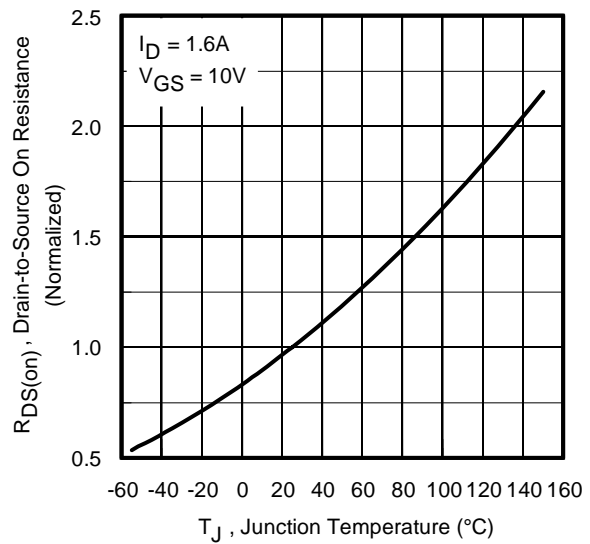


Fig 4. Normalized On-Resistance Vs. Temperature

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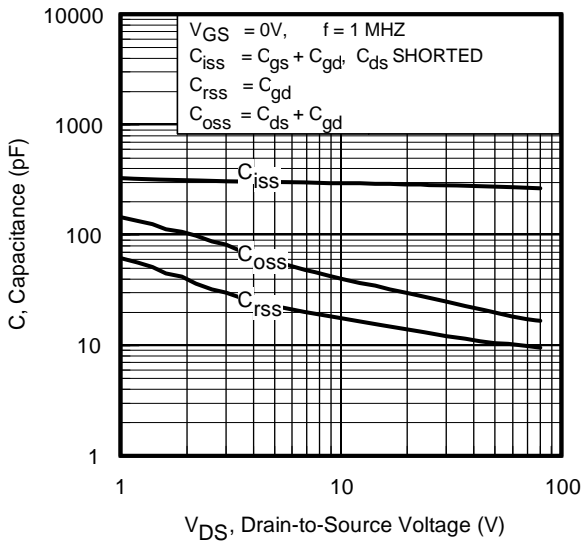


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

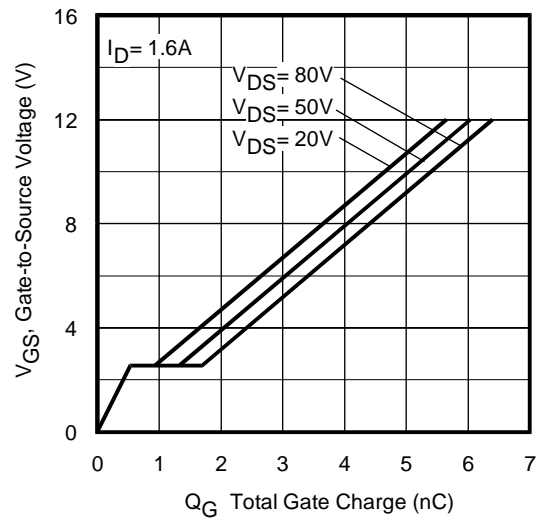


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

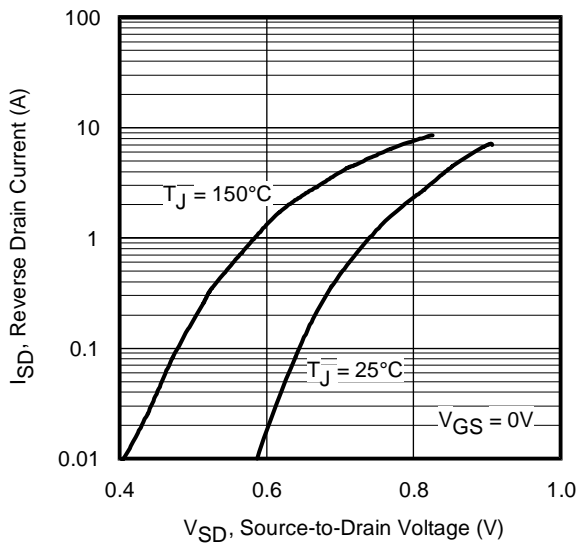


Fig 7. Typical Source-Drain Diode Forward Voltage

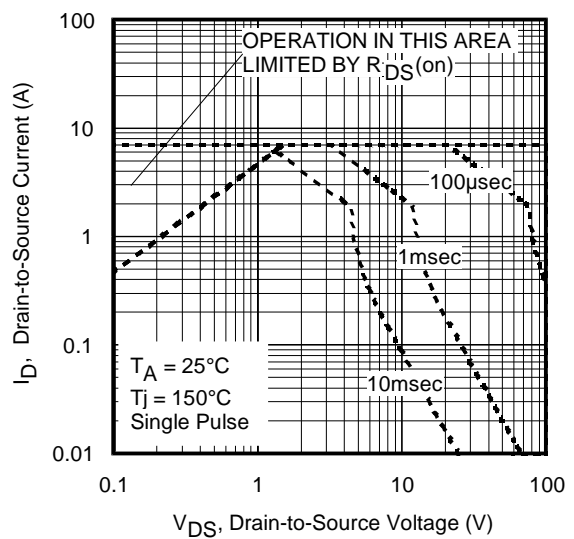


Fig 8. Maximum Safe Operating Area

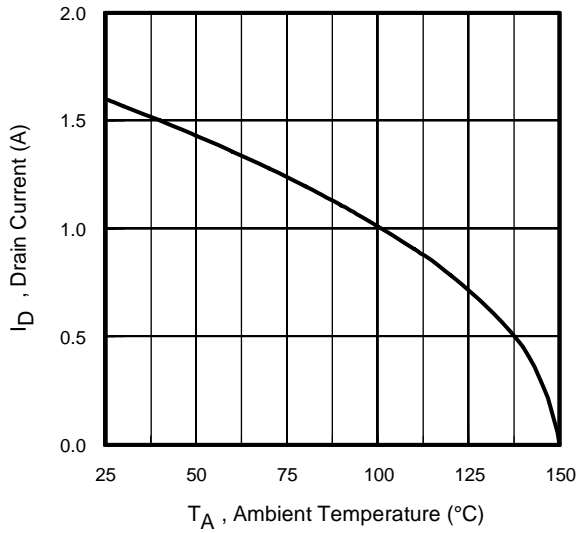


Fig 9. Maximum Drain Current Vs. Ambient Temperature

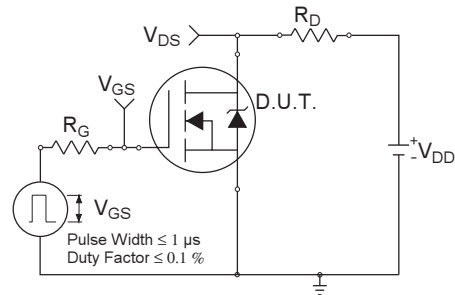


Fig 10a. Switching Time Test Circuit

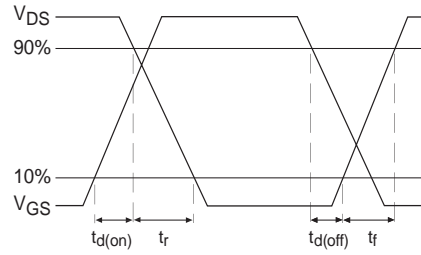


Fig 10b. Switching Time Waveforms

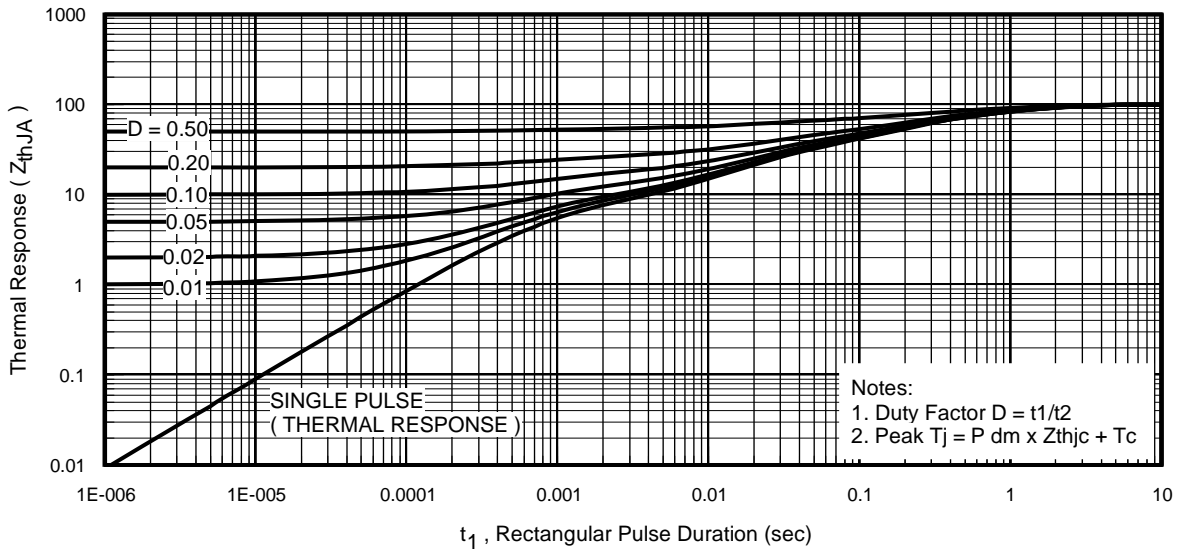


Fig 11. Typical Effective Transient Thermal Impedance, Junction-to-Ambient

IRLML0100TRPbF

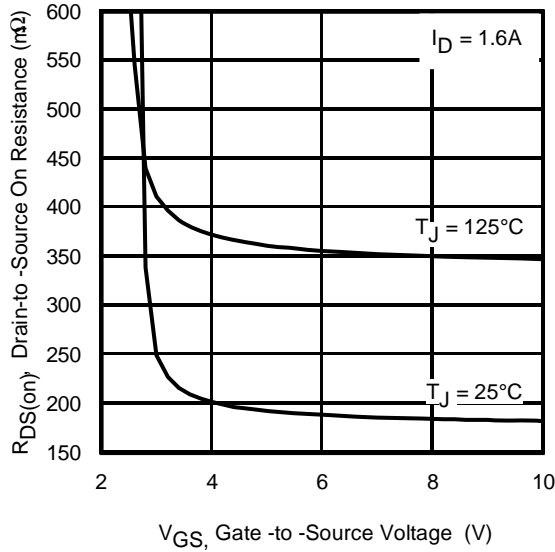


Fig 12. Typical On-Resistance Vs. Gate Voltage

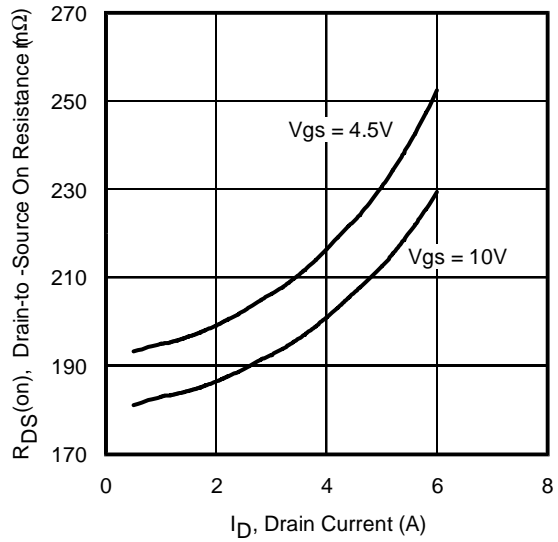


Fig 13. Typical On-Resistance Vs. Drain Current

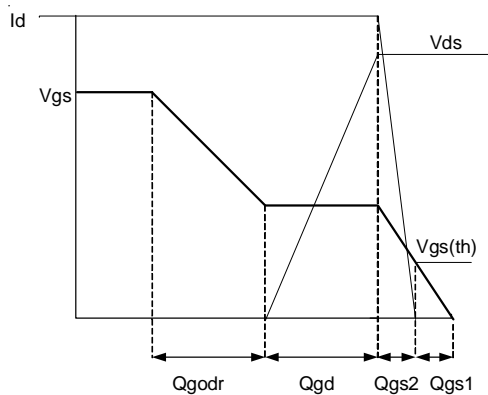


Fig 14a. Basic Gate Charge Waveform

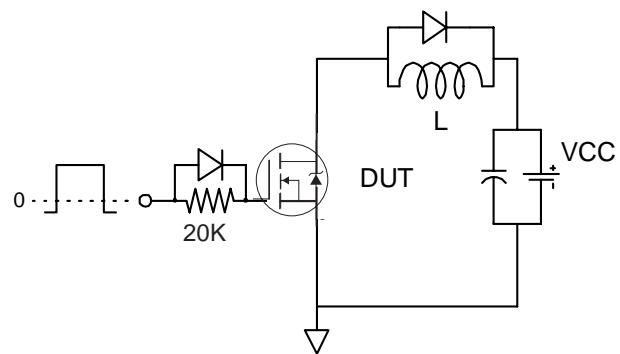


Fig 14b. Gate Charge Test Circuit

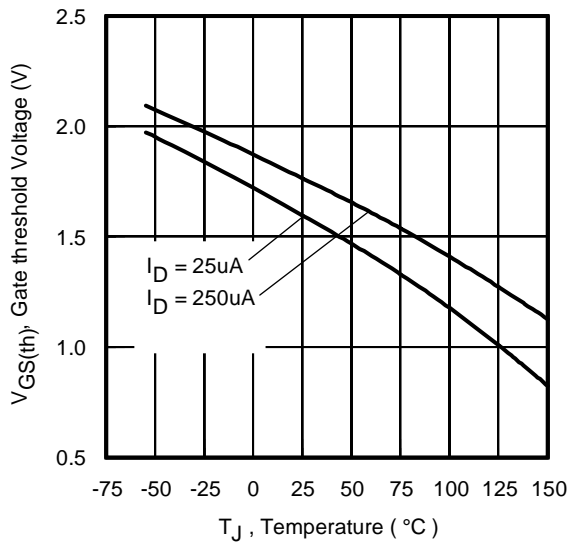


Fig 15. Typical Threshold Voltage Vs. Junction Temperature

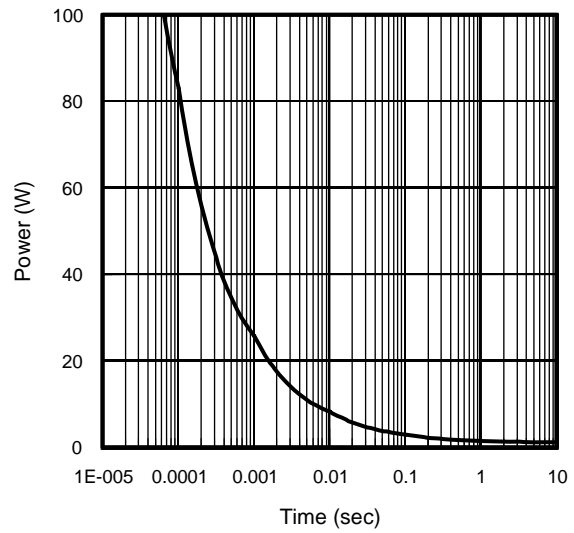


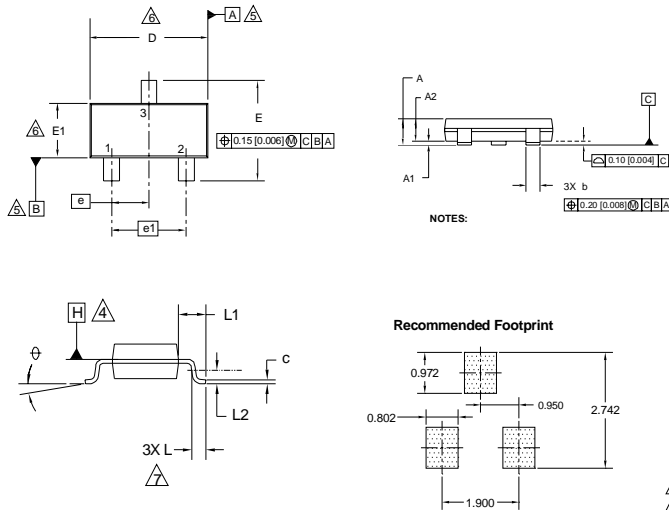
Fig 16. Typical Power Vs. Time

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Micro3 (SOT-23) Package Outline

Dimensions are shown in millimeters (inches)



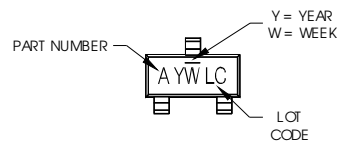
| DIMENSIONS | | | | |
|------------|-------------|------|--------|-------|
| SYMBOL | MILLIMETERS | | INCHES | |
| | MIN | MAX | MIN | MAX |
| A | 0.89 | 1.12 | 0.035 | 0.044 |
| A1 | 0.01 | 0.10 | 0.0004 | 0.004 |
| A2 | 0.88 | 1.02 | 0.035 | 0.040 |
| b | 0.30 | 0.50 | 0.012 | 0.020 |
| c | 0.08 | 0.20 | 0.003 | 0.008 |
| D | 2.80 | 3.04 | 0.110 | 0.120 |
| E | 2.10 | 2.64 | 0.083 | 0.104 |
| E1 | 1.20 | 1.40 | 0.047 | 0.055 |
| e | 0.95 | BSC | 0.037 | BSC |
| e1 | 1.90 | BSC | 0.075 | BSC |
| L | 0.40 | 0.60 | 0.016 | 0.024 |
| L1 | 0.54 | REF | 0.021 | REF |
| L2 | 0.25 | BSC | 0.010 | BSC |
| ⌀ | 0 | 8 | 0 | 8 |

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES)
3. CONTROLLING DIMENSION: MILLIMETER
4. DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE
5. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H
6. DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H. DIMENSIONS DOES NOT INCLUDE MOLD PROTRUSIONS OR INTERLEAD FLASH. MOLD PROTRUSIONS OR INTERLEAD FLASH SHALL NOT EXCEED 0.25 MM (0.010 INCH) PER SIDE.
7. DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-236 AB.

Micro3 (SOT-23/TO-236AB) Part Marking Information

Notes: This part marking information applies to devices produced after 02/26/2001

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

- A = IRLML2402
- B = IRLML2803
- C = IRLML6302
- D = IRLML5103
- E = IRLML6402
- F = IRLML6401
- G = IRLML2502
- H = IRLML5203
- I = IRLML0030
- J = IRLML2030
- K = IRLML0100
- L = IRLML0060
- M = IRLML0040
- N = IRLML2060

Note: A line above the work week (as shown here) indicates Lead-Free.

| YEAR | Y | WORK WEEK | W |
|------|---|-----------|---|
| 2001 | 1 | 01 | A |
| 2002 | 2 | 02 | B |
| 2003 | 3 | 03 | C |
| 2004 | 4 | 04 | D |
| 2005 | 5 | | |
| 2006 | 6 | | |
| 2007 | 7 | | |
| 2008 | 8 | | |
| 2009 | 9 | | |
| 2010 | 0 | 24 | X |
| | | 25 | Y |
| | | 26 | Z |

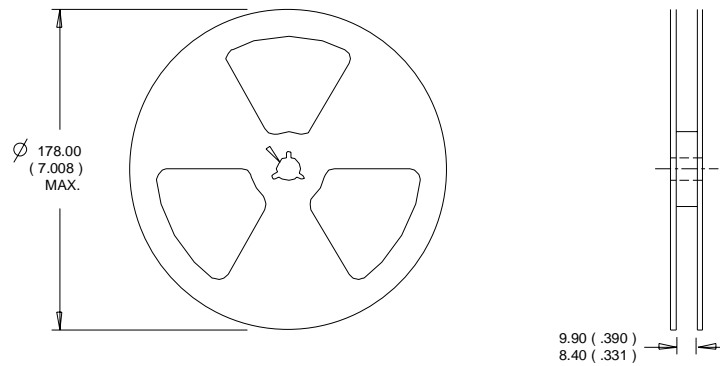
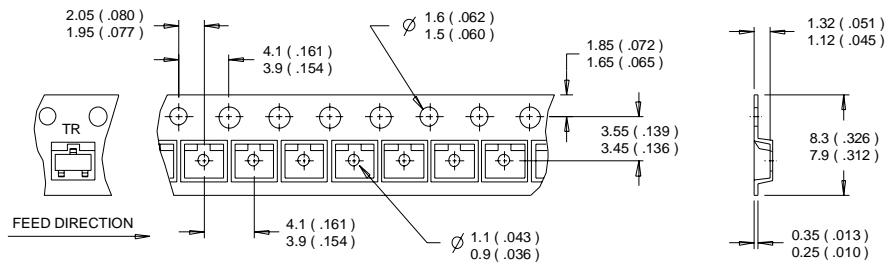
W = (27-52) IF PRECEDED BY A LETTER

| YEAR | Y | WORK WEEK | W |
|------|---|-----------|---|
| 2001 | A | 27 | A |
| 2002 | B | 28 | B |
| 2003 | C | 29 | C |
| 2004 | D | 30 | D |
| 2005 | E | | |
| 2006 | F | | |
| 2007 | G | | |
| 2008 | H | | |
| 2009 | J | | |
| 2010 | K | 50 | X |
| | | 51 | Y |
| | | 52 | Z |

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
 1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

IRLML0100TRPbF

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IR Rectifier

| Orderable part number | Package Type | Standard Pack | | Note |
|-----------------------|--------------|---------------|----------|------|
| | | Form | Quantity | |
| IRLML0100TRPbF | Micro3 | Tape and Reel | 3000 | |

Qualification information[†]

| | | | |
|----------------------------|---|---|--|
| Qualification level | Consumer ^{††} (per JEDEC JESD47F ^{†††} guidelines) | | |
| Moisture Sensitivity Level | Micro3 | MSL 1 (per IPC/JEDEC J-STD-020D ^{†††}) | |
| RoHS compliant | Yes | | |

- † Qualification standards can be found at International Rectifier's web site
<http://www.irf.com/product-info/reliability>
- †† Higher qualification ratings may be available should the user have such requirements.
Please contact your International Rectifier sales representative for further information:
<http://www.irf.com/whoto-call/salesrep/>
- ††† Applicable version of JEDEC standard at the time of product release.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width ≤ 400µs; duty cycle ≤ 2%.
- ③ Surface mounted on 1 in square Cu board
- ④ Refer to [application note #AN-994](#).

Data and specifications subject to change without notice.

International
IR Rectifier

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TAC Fax: (310) 252-7903

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